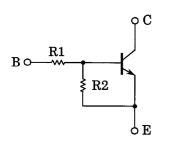
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

#### RN1221,RN1222,RN1223,RN1224 RN1225,RN1226,RN1227

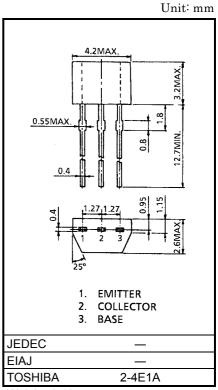
Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- High current type (I<sub>C(MAX)</sub> = 800mA)
- With built-in bias resistors.
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Low VCE (sat)
- Complementary to RN2221~2227

#### **Equivalent Circuit**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1221	1	1
RN1222	2.2	2.2
RN1223	4.7	4.7
RN1224	10	10
RN1225	0.47	10
RN1226	1	10
RN1227	2.2	10



Weight: 0.13g

### **Maximum Ratings (Ta = 25°C)**

Characteristi	Symbol	Rating	Unit		
Collector-base voltage	RN1221~1227	$V_{CBO}$	50	V	
Collector-emitter voltage	KIN IZZ I 12Z I	$V_{CEO}$	50	V	
	RN1221~1224		10	V	
Emitter-base voltage	RN1225, 1226	V <sub>EBO</sub>	5		
	RN1227		6		
Collector current		I <sub>c</sub>	800	mA	
Collector power dissipation	RN1221~1227	Pc	300	mW	
Junction temperature	1001221-1221	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

1

2001-06-07

# **TOSHIBA** RN1221,RN1222,RN1223,RN1224,RN1225,RN1226,RN1227

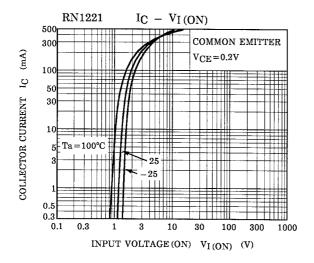
## Electrical Characteristics (Ta = 25°C)

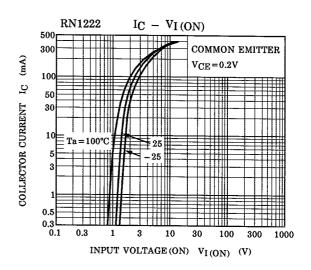
Characteris	stic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN1221~1227	I <sub>CBO</sub>	_	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	nA
	RN1221~1221	I <sub>CEO</sub>	_	V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	_	_	500	
Emitter cut-off current	RN1221	l <sub>EBO</sub>	_	V <sub>EB</sub> = 10V, I <sub>C</sub> = 0	3.85	_	7.14	
	RN1222		_		1.75	_	3.25	mA
	RN1223		_		0.82	_	1.52	
	RN1224		_		0.38	_	0.71	
	RN1225		_	V 5V 1 0	0.365	_	0.682	
	RN1226		_	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	0.35	_	0.65	
	RN1227		_	V <sub>EB</sub> = 6V, I <sub>C</sub> = 0	0.378		0.703	
	RN1221		_		60	_	_	_
	RN1222	h <sub>FE</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA	65	_	_	
DC current gain	RN1223		_		70	_	_	
	RN1224		_		90	_	_	
	RN1225		_		90	_	_	
	RN1226		_		90	_	_	
	RN1227		_		90	_	_	
Collector-emitter	RN1221	V <sub>CE (sat)</sub>		I <sub>C</sub> = 50mA, I <sub>B</sub> = 2mA		0.25	V	
saturation voltage	RN1222~1227		-	I <sub>C</sub> = 50mA, I <sub>B</sub> = 1mA		_ 0	0.25	V
	RN1221	Vi (on)	_	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 100mA	1.0	-	3.5	V
	RN1222		_		1.4		4.5	
	RN1223		_		2.0		6.5	
Input voltage (ON)	RN1224		_		3.0		12.0	
	RN1225		_		0.6	1	2.0	
	RN1226		_		0.7	1	2.5	
	RN1227		_		1.0		3.0	
Input voltage (OFF)	RN1221~1224		_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA	0.8	_	1.3	V
	RM1225, 1226		_		0.4		0.8	
	RN1227		_		0.5	-	1.0	
Translation frequency	RN1221~1227	f <sub>T</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 20mA	_	300	_	MHz
Collector output capacitance	RN1221~1227	C <sub>ob</sub>	_	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz	_	7	_	pF

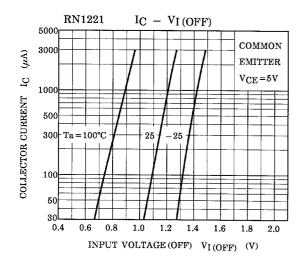
# **TOSHIBA** RN1221,RN1222,RN1223,RN1224,RN1225,RN1226,RN1227

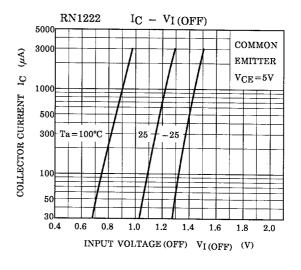
### Electrical Characteristics (Ta = 25°C)

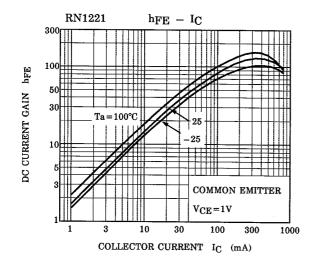
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input resistor	RN1221	R1	_	_	0.7	1.0	1.3	kΩ
	RN1222		_		1.54	2.2	2.86	
	RN1223		_		3.29	4.7	6.11	
	RN1224		_		7	10	13	
	RN1225		_		0.329	0.47	0.61	
	RN1226		_		0.7	1.0	1.3	
	RN1227		_		1.54	2.2	2.86	
Resistor ratio	RN1221~1224	R1/R2	_	_	0.9	1.0	1.1	_
	RN1225		_		0.0423	0.047	0.0517	
	RN1226		_		0.09	0.1	0.11	
	RN1227		_		0.2	0.22	0.24	

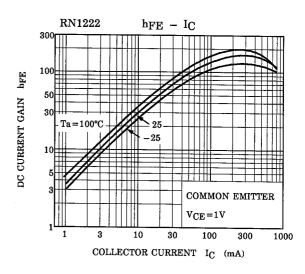


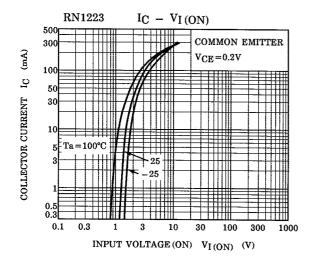


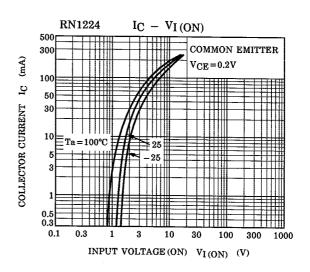


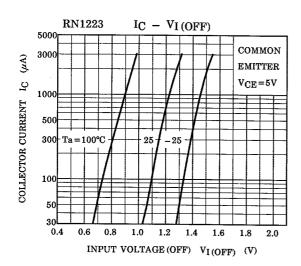


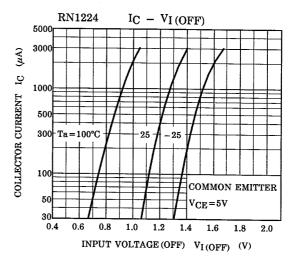


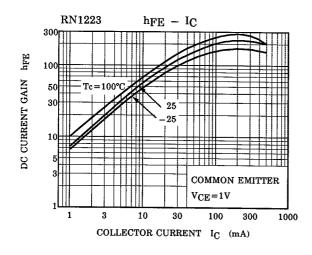


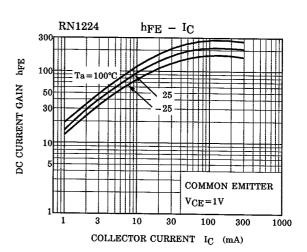


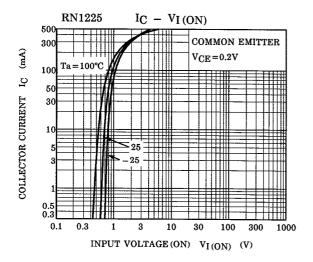


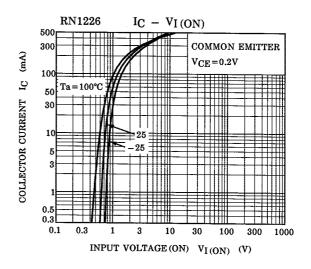


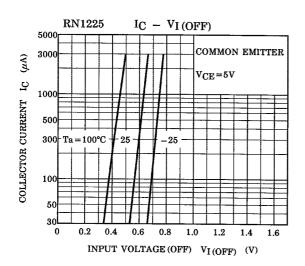


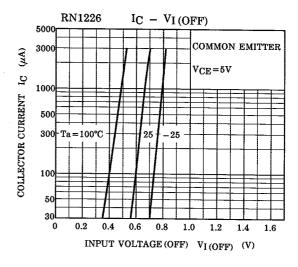


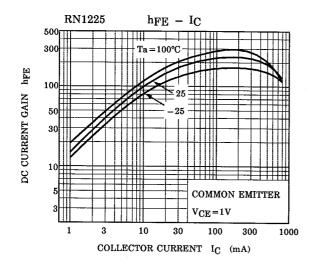


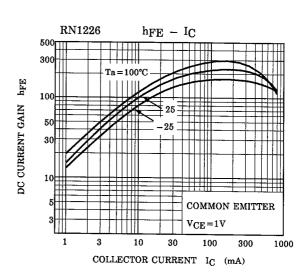


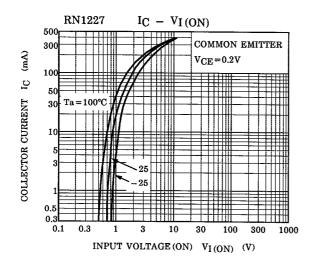


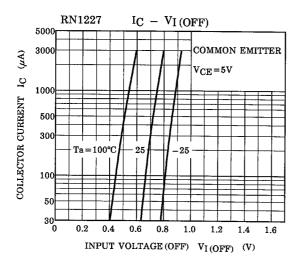


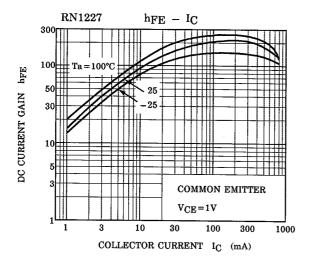












#### RESTRICTIONS ON PRODUCT USE

000707EAA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
  rights of the third parties which may result from its use. No license is granted by implication or otherwise under
  any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.